



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

|                                   |        |
|-----------------------------------|--------|
| $V_{DS}$                          | 30V    |
| $I_D$                             | 3.6A   |
| $R_{DS(ON)}$ ( at $V_{GS}=10V$ )  | 33mohm |
| $R_{DS(ON)}$ ( at $V_{GS}=4.5V$ ) | 48mohm |
| 100% $V_{DS}$ Tested              |        |

### General Description

Trench Power MV MOSFET technology  
High Power and current handing capability  
Moisture Sensitivity Level 1  
Epoxy Meets UL 94 V-0 Flammability Rating  
Halogen Free

### Applications

PWM application  
Load switch

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|-----------|--------|-------|------|
|-----------|--------|-------|------|







# YJL2304A

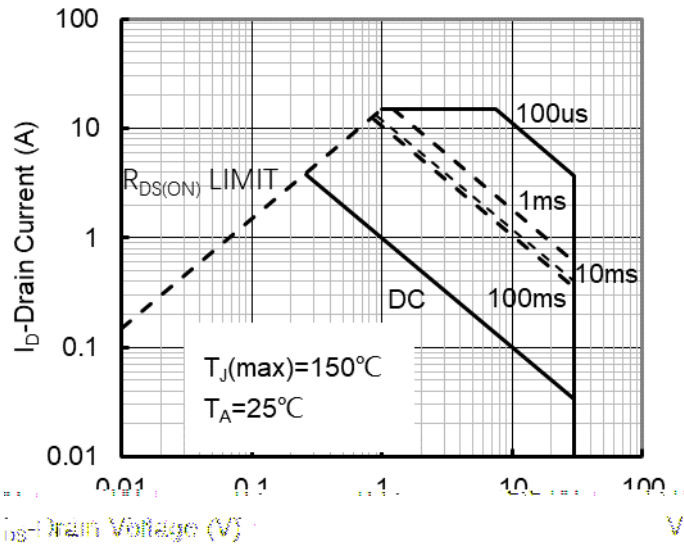


Figure7. Safe Operation Area

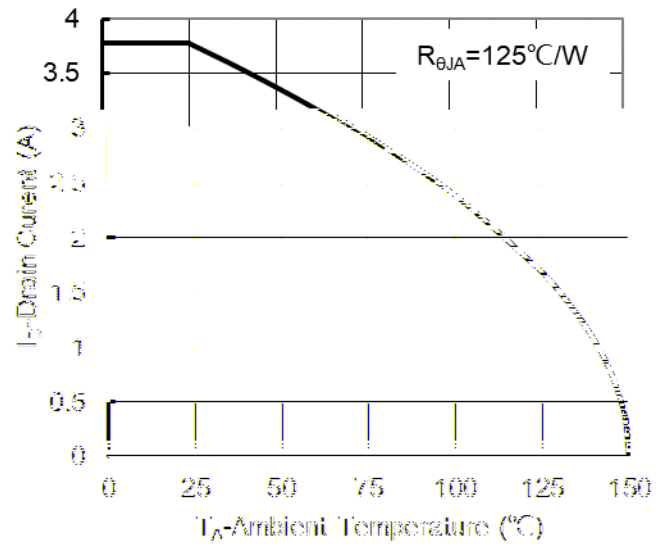


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

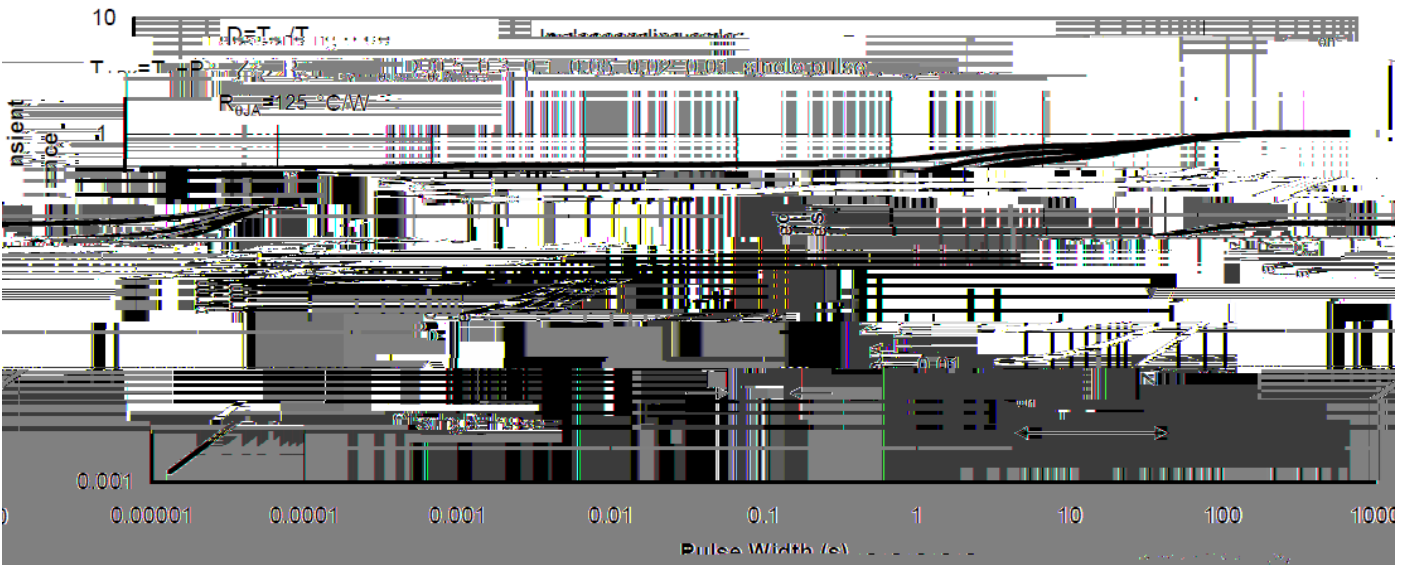
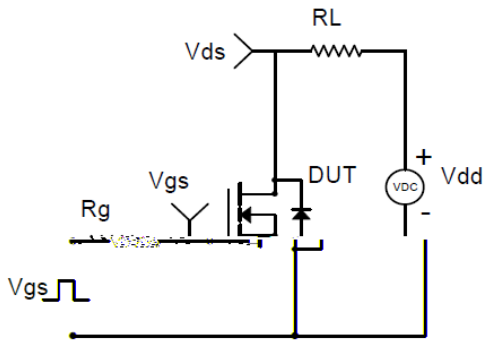
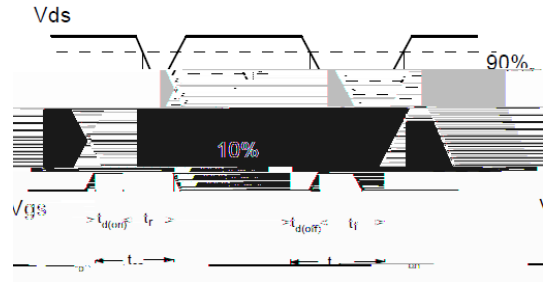


Figure9. Normalized Maximum Transient Thermal Impedance

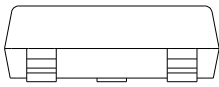
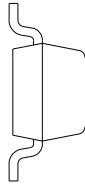
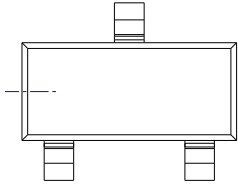


**Resistive**





SOT-23 Package information



UNIT mm



## Disclaimer

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